

ZHS50-300/100
HIGH POWER AMPLIFIER FOR LTE BAND
50 MHz – 300 MHz



Designed for Testing, labs and Special purposes, transmitters, this amplifier incorporates microstrip technology and LDMOS device to enhance ruggedness and reliability.

Size (base plate): 6" x 4" x 3"

- 50 MHz-300 MHz • 48 Volts
- Input/Output 50 Ω
- Pout : 100 W min
- Standby Curent 70 mA
- Max curent 9 A
- Gain : 23 dB typ
- Class B

Electrical Specifications:

ELECTRICAL SPECIFICATIONS (Base Plate T. = 45 °C, 50Ω loaded, Vd = 48 V)

ELECTRICAL				
Characteristics	Min	Typ.	Max	Unit
Operating Frequency Range	45		330	MHz
Fundamental Output Power	100			W
Power Input		1.5	2	W
Power Gain (100W output)		23		dB
I Drain		8.5	9	A
Collector Efficiency (Load 50Ω)		80		%
Input VSWR		1.3:1	1.7:1	
Insertion Phase Variation (Unit to Unit)		±10		Degrees
Power Gain Variation (Unit to Unit)		±1		dB
F2 Second Harmonic	-35	-40		dB
F3 Third Harmonic		-40		dB

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